

TOSHIBA Diode Silicon Epitaxial Schottky Barrier Type

1SS374

High Speed Switching Application

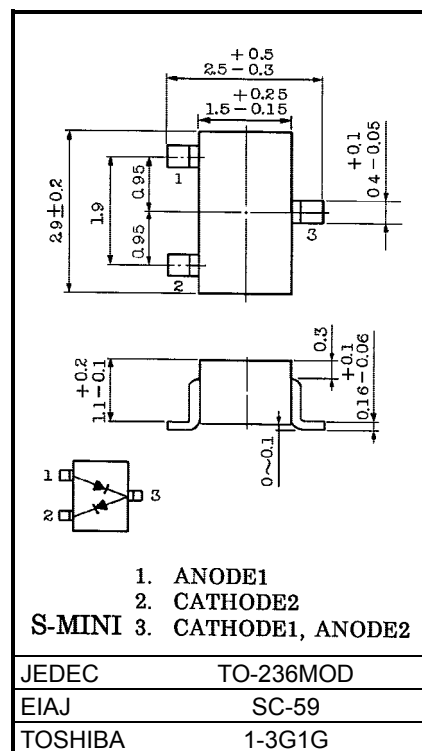
Unit: mm

- Small package
- Low forward voltage: $V_F(2) = 0.23V$ (typ.) @ $I_F = 5mA$

Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Maximum (peak) reverse Voltage	V_{RM}	15	V
Reverse voltage	V_R	10	V
Maximum (peak) forward current	I_{FM}	200 *	mA
Average forward current	I_O	100 *	mA
Surge current (10ms)	I_{FSM}	1 *	A
Power dissipation	P	150	mW
Junction temperature	T_j	125	°C
Storage temperature range	T_{stg}	-55~125	°C
Operating temperature range	T_{opr}	-40~100	°C

* Unit rating. Total rating = unit rating × 0.7



Weight: 0.012g

Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Forward voltage	$V_F(1)$	—	$I_F = 1mA$	—	0.18	—	V
	$V_F(2)$	—	$I_F = 5mA$	—	0.23	0.30	
	$V_F(3)$	—	$I_F = 100mA$	—	0.35	0.50	
Reverse current	I_R	—	$V_R = 10V$	—	—	20	μA
Total capacitance	C_T	—	$V_R = 0, f = 1MHz$	—	20	40	pF

Marking

